

# Asynchronous, Cascadable 8K/16K/32K/64K x9 FIFOs

## Features

- High-speed, low-power, first-in first-out (FIFO) memories
- 8K x 9 FIFO (CY7C460A)
- 16K x 9 FIFO (CY7C462A)
- 32K x 9 FIFO (CY7C464A)
- 64K x 9 FIFO (CY7C466A)
- 10 ns access times, 20 ns read/write cycle times
- High-speed 50 MHz read/write independent of depth/width
- Low operating power
  - $I_{CC} = 60$  mA
  - $I_{SB} = 2$  mA
- Asynchronous read/write
- Empty and Full flags
- Half Full flag (in standalone mode)
- Retransmit (in standalone mode)
- TTL-compatible
- Width and Depth Expansion Capability
- 5V  $\pm 10\%$  supply
- PLCC, LCC, 300-mil and 600-mil DIP packaging
- Three-state outputs
- Pin compatible density upgrade to CY7C42X/46X family
- Pin compatible and functionally equivalent to IDT7205, IDT7206, IDT7207, IDT7208

## Functional Description

The CY7C460A, CY7C462A, CY7C464A, and CY7C466A are respectively, 8K, 16K, 32K, and 64K words by 9-bit wide first-in-first-out (FIFO) memories. Each FIFO memory is organized such that the data is read in the same sequential order that it was written. Full and Empty flags are provided to prevent overrun and underrun. Three additional pins are also provided to facilitate unlimited expansion in width, depth, or both. The depth expansion technique steers the control signals from one device to another by passing tokens.

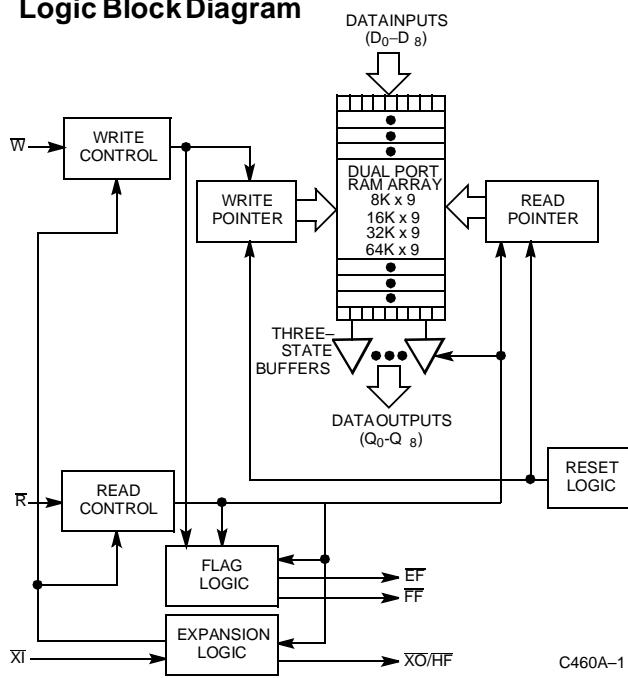
The read and write operations may be asynchronous; each can occur at a rate of up to 50 MHz. The write operation occurs when the write (W) signal is LOW. Read occurs when read (R) goes LOW. The nine data outputs go to the high-impedance state when R is HIGH.

A Half Full (HF) output flag is provided that is valid in the standalone (single device) and width expansion configurations. In the depth expansion configuration, this pin provides the expansion out (XO) information that is used to tell the next FIFO that it will be activated.

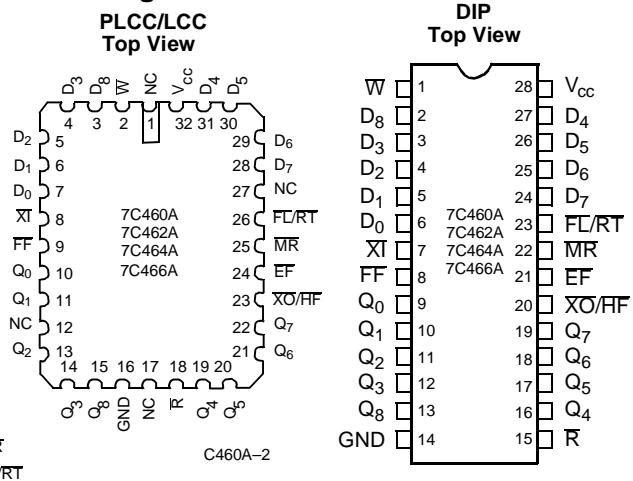
In the standalone and width expansion configurations, a LOW on the retransmit (RT) input causes the FIFOs to retransmit the data. Read enable (R) and write enable (W) must both be HIGH during a retransmit cycle, and then R is used to access the data.

The CY7C460A, CY7C462A, CY7C464A, and CY7C466A are fabricated using Cypress's advanced 0.5 $\mu$  RAM3 CMOS technology. Input ESD protection is greater than 2000V and latch-up is prevented by careful layout and the use of guard rings.

## Logic Block Diagram



## Pin Configurations





## Selection Guide

	7C460A-10 7C462A-10 7C464A-10 7C466A-10	7C460A-15 7C462A-15 7C464A-15 7C466A-15	7C460A-25 7C462A-25 7C464A-25 7C466A-25
Frequency (MHz)	50	40	28.5
Maximum Access Time (ns)	10	15	25

## Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....  $-65^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$

Ambient Temperature with Power Applied .....  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$

Supply Voltage to Ground Potential .....  $-0.5\text{V}$  to  $+7.0\text{V}$

DC Voltage Applied to Outputs in High Z State .....  $-0.5\text{V}$  to  $+7.0\text{V}$

DC Input Voltage .....  $-0.5\text{V}$  to  $+7.0\text{V}$

Power Dissipation ..... 1.0W

Output Current, into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... >2001V (per MIL-STD-883, Method 3015)

Latch-Up Current ..... >200 mA

## Operating Range

Range	Ambient Temperature	V <sub>CC</sub>
Commercial	$0^{\circ}\text{C}$ to $+70^{\circ}\text{C}$	$5\text{V} \pm 10\%$
Industrial	$-40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$	$5\text{V} \pm 10\%$
Military <sup>[1]</sup>	$-55^{\circ}\text{C}$ to $+125^{\circ}\text{C}$	$5\text{V} \pm 10\%$

Electrical Characteristics Over the Operating Range<sup>[2]</sup>

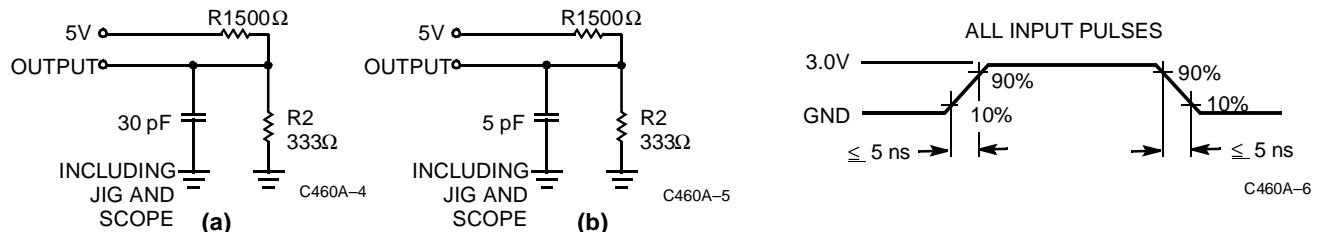
Parameter	Description	Test Conditions	7C460A/462A/464A/466A (-10,-15,-25)		Unit
			Min.	Max.	
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min., I <sub>OH</sub> = $-2.0\text{ mA}$	2.4		V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min., I <sub>OL</sub> = $8.0\text{ mA}$		0.4	V
V <sub>IH</sub>	Input HIGH Voltage		2.2	V <sub>CC</sub>	V
V <sub>IL</sub>	Input LOW Voltage		-0.5	0.8	V
I <sub>IX</sub>	Input Leakage Current	GND $\leq$ V <sub>I</sub> $\leq$ V <sub>CC</sub>	-10	+10	$\mu\text{A}$
I <sub>OZ</sub>	Output Leakage Current	R $\geq$ V <sub>IH</sub> , GND $\leq$ V <sub>O</sub> $\leq$ V <sub>CC</sub>	-10	+10	$\mu\text{A}$
I <sub>CC</sub>	Operating Current	V <sub>CC</sub> = Max., I <sub>OUT</sub> = $0\text{ mA}$ , Freq=20MHz		60	mA
I <sub>SB</sub>	Standby Current	All Inputs = V <sub>CC</sub> - $.2\text{V}$ , Freq=0MHz		2	mA

Capacitance<sup>[4]</sup>

Parameter	Description	Test Conditions	Max.	Unit
C <sub>IN</sub>	Input Capacitance	T <sub>A</sub> = $25^{\circ}\text{C}$ , f = 1 MHz, V <sub>CC</sub> = $4.5\text{V}$	10	pF
C <sub>OUT</sub>	Output Capacitance		12	pF

## Notes:

1. T<sub>A</sub> is the "instant on" case temperature.
2. See the last page of this specification for Group A subgroup testing information.
3. For test purposes, not more than one output at a time should be shorted. Short circuit test duration should not exceed 1 second.
4. Tested initially and after any design or process changes that may affect these parameters.

**AC Test Loads and Waveforms**


Equivalent to:      THÉVENIN EQUIVALENT  
 $200\Omega$   
 OUTPUT  $\rightarrow$  2V

**Switching Characteristics** Over the Operating Range<sup>[2,5]</sup>

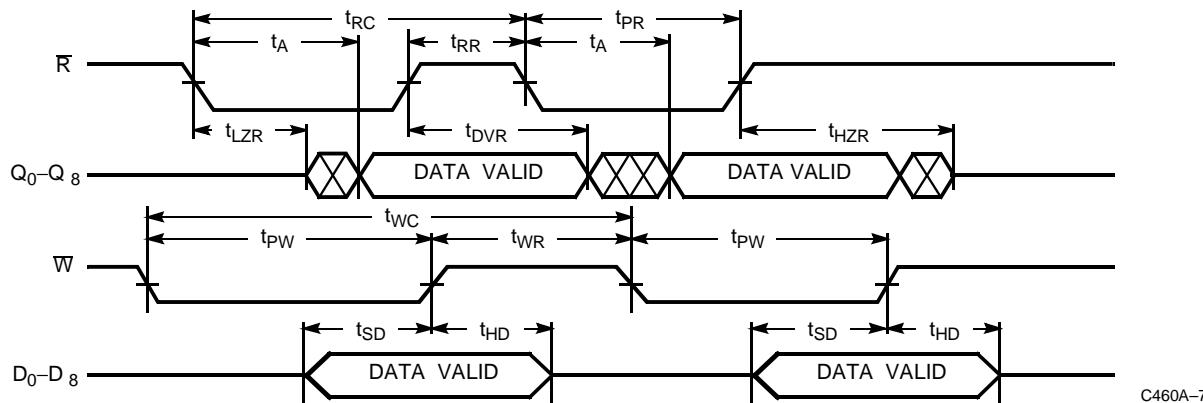
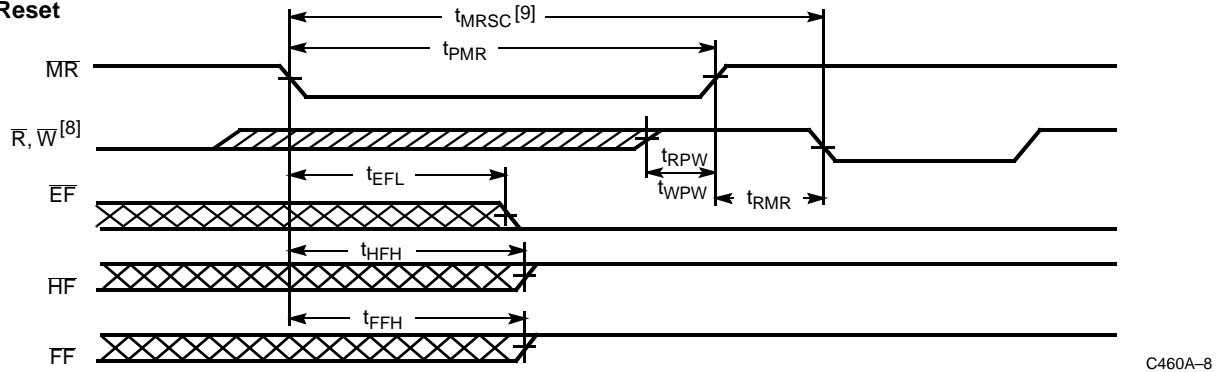
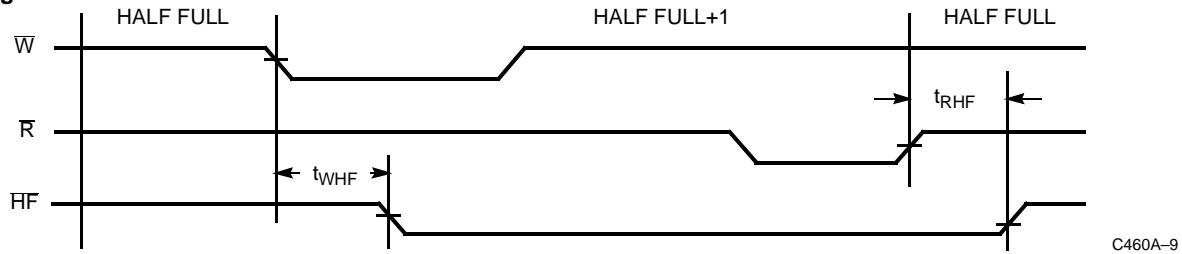
Parameter	Description	7C460A-10 7C462A-10 7C464A-10 7C466A-10		7C460A-15 7C462A-15 7C464A-15 7C466A-15		7C460A-25 7C462A-25 7C464A-25 7C466A-25		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
$t_{RC}$	Read Cycle Time	20		25		35		ns
$t_A$	Access Time		10		15		25	ns
$t_{RR}$	Read Recovery Time	10		10		10		ns
$t_{PR}$	Read Pulse Width	10		15		25		ns
$t_{LZR}$	Read LOW to Low Z	3		3		3		ns
$t_{DVR}^{[6]}$	Data Valid After Read HIGH	3		3		3		ns
$t_{HZR}^{[6]}$	Read HIGH to High Z		15		15		18	ns
$t_{WC}$	Write Cycle Time	20		25		35		ns
$t_{PW}$	Write Pulse Width	10		15		25		ns
$t_{HWZ}$	Write HIGH to Low Z	5		5		5		ns
$t_{WR}$	Write Recovery Time	10		10		10		ns
$t_{SD}$	Data Set-Up Time	9		9		9		ns
$t_{HD}$	Data Hold Time	0		0		0		ns
$t_{MRSC}$	MR Cycle Time	20		25		35		ns
$t_{PMR}$	MR Pulse Width	10		15		25		ns
$t_{RMR}$	MR Recovery Time	10		10		10		ns
$t_{RPW}$	Read HIGH to $\overline{MR}$ HIGH	10		15		25		ns
$t_{WPW}$	Write HIGH to $\overline{MR}$ HIGH	10		15		25		ns
$t_{RTC}$	Retransmit Cycle Time	20		25		35		ns
$t_{PRT}$	Retransmit Pulse Width	10		15		25		ns
$t_{RTR}$	Retransmit Recovery Time	10		10		10		ns
$t_{EFL}$	MR to $\overline{EF}$ LOW		20		25		35	ns
$t_{HFH}$	MR to $\overline{HF}$ HIGH		20		25		35	ns
$t_{FFH}$	MR to $\overline{FF}$ HIGH		20		25		35	ns
$t_{REF}$	Read LOW to $\overline{EF}$ LOW		10		15		25	ns
$t_{RFF}$	Read HIGH to $\overline{FF}$ HIGH		10		15		25	ns
$t_{WEF}$	Write HIGH to $\overline{EF}$ HIGH		10		15		25	ns
$t_{WFF}$	Write LOW to $\overline{FF}$ LOW		10		15		25	ns
$t_{WHF}$	Write LOW to $\overline{HF}$ LOW		10		15		35	ns

**Switching Characteristics** Over the Operating Range<sup>[2,5]</sup> (continued)

Parameter	Description	7C460A-10		7C460A-15		7C460A-25		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
$t_{RHF}$	Read HIGH to $\overline{FF}$ HIGH		10		15		35	ns
$t_{RAE}$	Effective Read from Write HIGH		10		15		25	ns
$t_{RPE}$	Effective Read Pulse Width After $\overline{EF}$ HIGH	10		15		25		ns
$t_{WAF}$	Effective Write from Read HIGH		10		15		25	ns
$t_{WPF}$	Effective Write Pulse Width After $\overline{FF}$ HIGH	10		15		25		ns
$t_{XOL}$	Expansion Out LOW Delay from Clock		10		15		25	ns
$t_{XOH}$	Expansion Out HIGH Delay from Clock		10		15		25	ns

**Notes:**

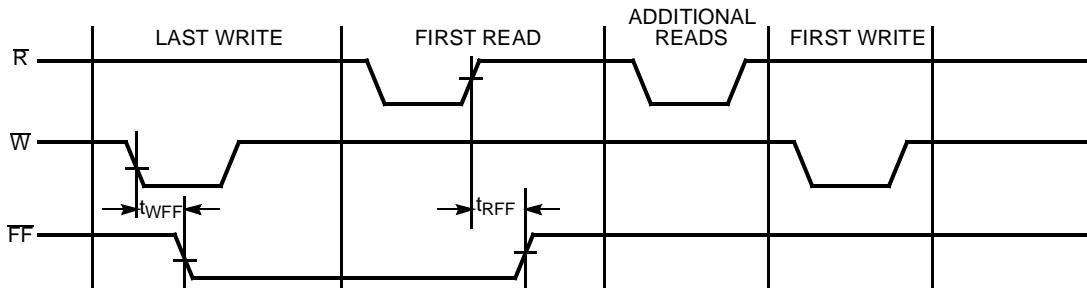
5. Test conditions assume signal transmission time of 5 ns or less, timing reference levels of 1.5V and output loading of the specified  $I_{OL}/I_{OH}$  and 30-pF load capacitance, as in part (a) of AC Test Load, unless otherwise specified.
6.  $t_{HZR}$  and  $t_{DVR}$  use capacitance loading as in part (b) of AC Test Load.

**Switching Waveforms<sup>[7]</sup>**
**Asynchronous Read and Write**

**Master Reset**

**Half Full Flag**

**Notes:**

7. A HIGH-to-LOW transition of either the write or read strobe causes a HIGH-to-LOW transition of the responding flag. Correspondingly, a LOW-to-HIGH strobe transition causes a LOW-to-HIGH flag transition.
8. W and R = V<sub>IH</sub> around the rising edge of MR.
9. t<sub>MRSC</sub> = t<sub>PMR</sub> + t<sub>RMR</sub>

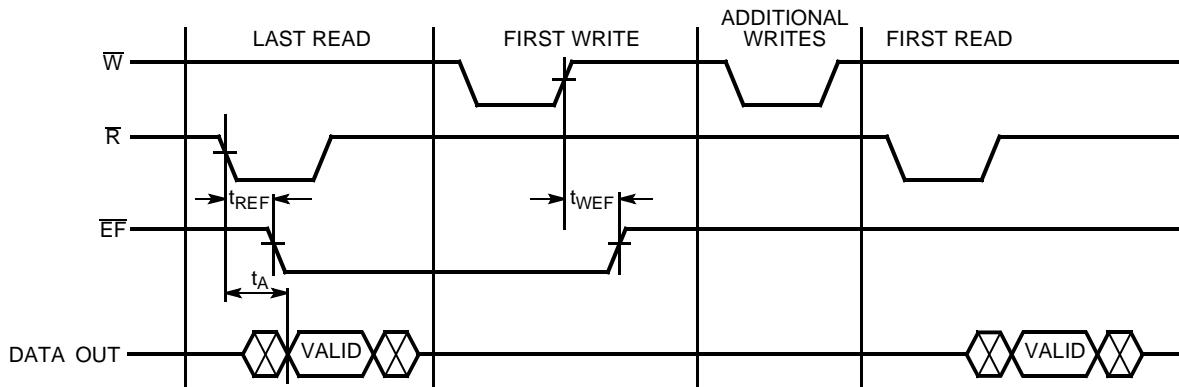
## Switching Waveforms<sup>[7]</sup> (continued)

## Last Write to First Read Full Flag



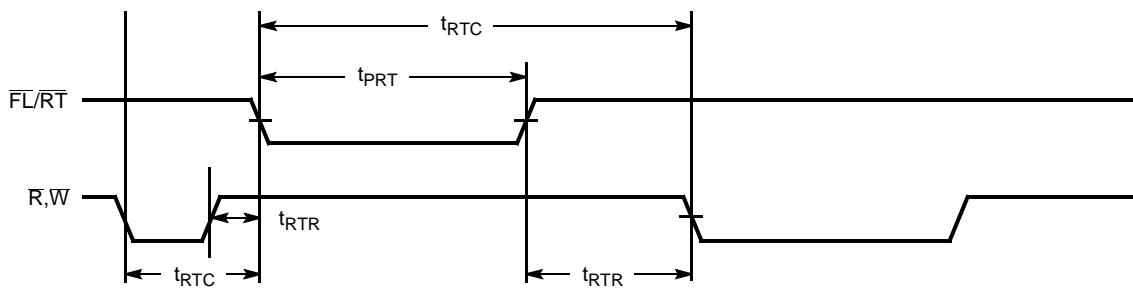
C460A-10

## Last READ to First WRITE Empty Flag



C460A-11

## Retransmit<sup>[10,11]</sup>



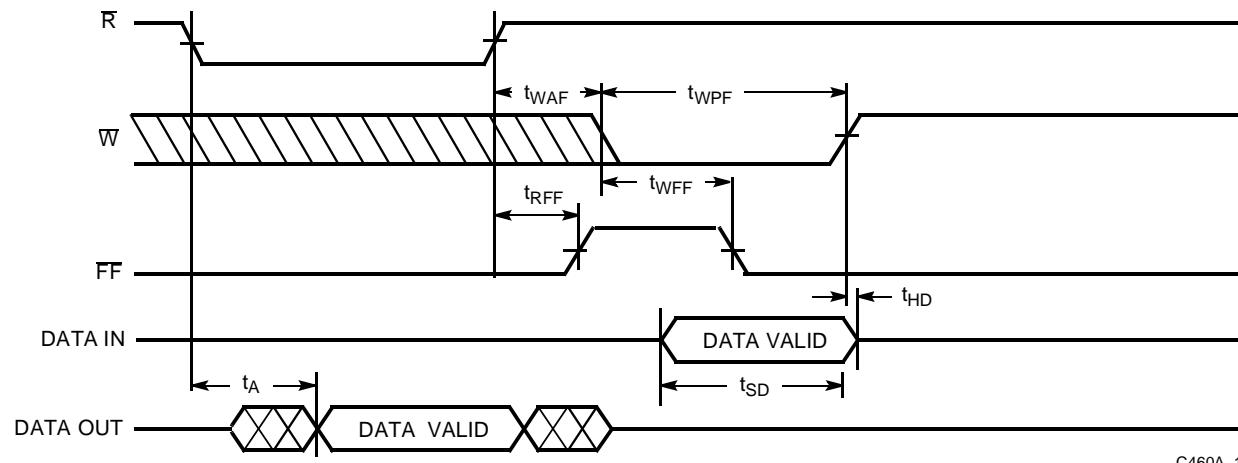
C460A-12

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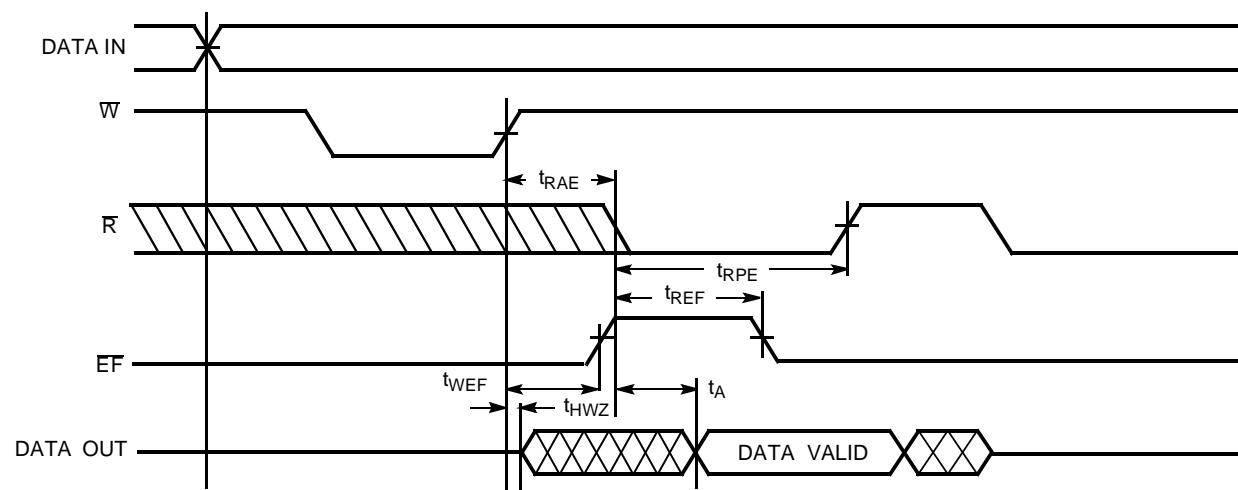
**Notes:**

Notes:

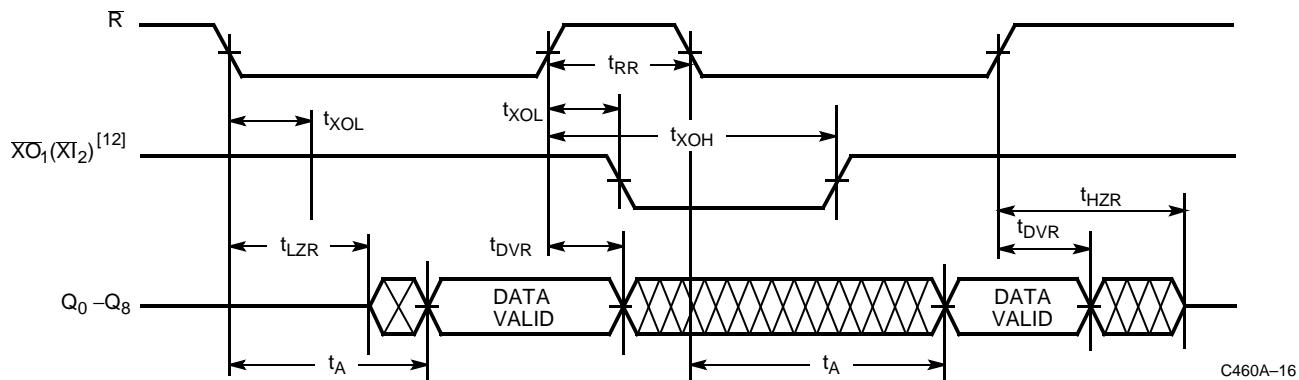
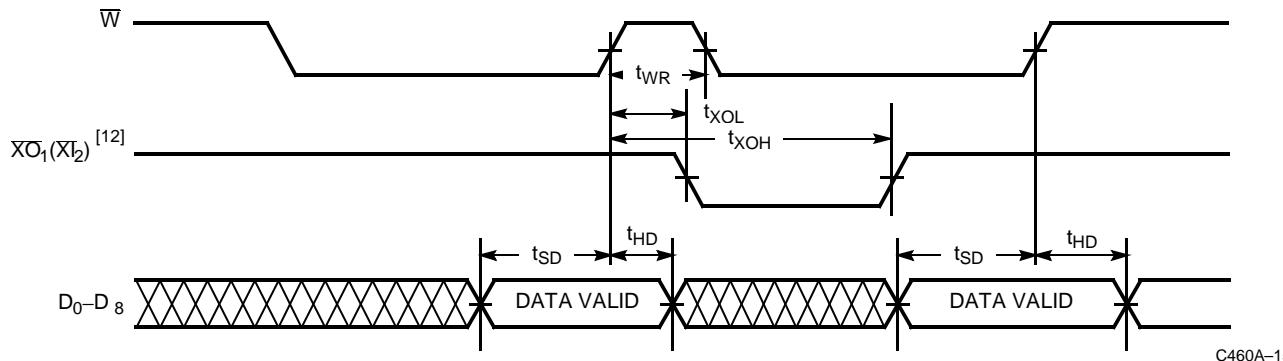
10.  $t_{RTC} = t_{PRT} + t_{RTR}$ .
11. EF, HF and FF may change state during retransmit as a result of the offset of the read and write pointers, but flags will be valid at  $t_{RTC}$ , except for the CY7C46x-20 (Military), whose flags will be valid after  $t_{RTC} + 10$  ns.

**Switching Waveforms<sup>[7]</sup> (continued)**
**Full Flag and Write Data Flow-Through Mode**


C460A-1

**Empty Flag and Read Data Flow-Through Mode**


C460A-14

**Switching Waveforms<sup>[7]</sup> (continued)**
**Expansion Timing Diagrams**

**Note:**

12. Expansion out of device 1 ( $\overline{XO}_1$ ) is connected to expansion in of device 2 ( $\overline{XI}_2$ ).

**Architecture**
**Resetting the FIFO**

Upon power up, the FIFO must be reset with a master reset ( $\overline{MR}$ ) cycle. This causes the FIFO to enter the empty condition signified by the Empty flag ( $\overline{EF}$ ) being LOW, and both the Half Full ( $\overline{HF}$ ), and Full flags ( $\overline{FF}$ ) being HIGH. Read ( $\overline{R}$ ) and write ( $\overline{W}$ ) must be HIGH  $t_{RPW}/t_{WPW}$  before and  $t_{RMR}$  after the rising edge of  $\overline{MR}$  for a valid reset cycle. If reading from the FIFO after a reset cycle is attempted, the outputs will all be in the high-impedance state.

**Writing Data to the FIFO**

The availability of at least one empty location is indicated by a HIGH  $\overline{FF}$ . The falling edge of  $\overline{W}$  initiates a write cycle. Data appearing at the inputs ( $D_0 - D_8$ )  $t_{SD}$  before and  $t_{HD}$  after the rising edge of  $\overline{W}$  will be stored sequentially in the FIFO.

The  $\overline{EF}$  LOW-to-HIGH transition occurs  $t_{WEF}$  after the first LOW-to-HIGH transition of  $\overline{W}$  for an empty FIFO.  $\overline{HF}$  goes LOW  $t_{WFF}$  after the falling edge of  $\overline{W}$  following the FIFO actually being half full. Therefore, the  $\overline{HF}$  is active once the FIFO is filled to half its capacity plus one word.  $\overline{HF}$  will remain LOW while less than one half of total memory is available for writing. The LOW-to-HIGH transition of  $\overline{HF}$  occurs  $t_{RHF}$  after the rising edge of  $\overline{R}$  when the FIFO goes from half full +1 to half full.  $\overline{HF}$  is available in standalone and width expansion modes.  $\overline{FF}$

goes LOW  $t_{WFF}$  after the falling edge of  $\overline{W}$ , during the cycle in which the last available location is filled. Internal logic prevents overrunning a full FIFO. Writes to a full FIFO are ignored and the write pointer is not incremented.  $\overline{FF}$  goes HIGH  $t_{RFF}$  after a read from a full FIFO.

**Reading Data from the FIFO**

The falling edge of  $\overline{R}$  initiates a read cycle if the  $\overline{EF}$  is not LOW. Data outputs ( $Q_0 - Q_8$ ) are in a high-impedance condition between read operations ( $\overline{R}$  HIGH), when the FIFO is empty, or when the FIFO is not the active device in the depth expansion mode.

When one word is in the FIFO, the falling edge of  $\overline{R}$  initiates a HIGH-to-LOW transition of  $\overline{EF}$ . When the FIFO is empty, the outputs are in a high-impedance state. Reads to an empty FIFO are ignored and do not increment the read pointer. From the empty condition, the FIFO can be read  $t_{WEF}$  after a valid write.

**Retransmit**

The retransmit feature is beneficial when transferring packets of data. It enables the receipt of data to be acknowledged by the receiver and retransmitted if necessary. The retransmit ( $\overline{RT}$ ) input is active in the standalone and width expansion modes. The retransmit feature is intended for use when a number of writes equal-to-or-less-than the depth of the FIFO

have occurred since the last  $\overline{MR}$  cycle. A LOW pulse on  $\overline{RT}$  resets the internal read pointer to the first physical location of the FIFO.  $\overline{R}$  and  $\overline{W}$  must both be HIGH while and tRTR after retransmit is LOW. With every read cycle after retransmit, previously accessed data is read and the read pointer incremented until equal to the write pointer. Full, Half Full, and Empty flags are governed by the relative locations of the read and write pointers and are updated during a retransmit cycle. Data written to the FIFO after activation of  $\overline{RT}$  are transmitted also.

The full depth of the FIFO can be repeatedly retransmitted.

## Standalone/Width Expansion Modes

Standalone and width expansion modes are set by grounding expansion in (XT) and tying first load (FL) to V<sub>CC</sub> prior to a MR cycle. FIFOs can be expanded in width to provide word widths greater than nine in increments of nine. During width expansion mode, all control line inputs are common to all devices, and flag outputs from any device can be monitored.

### Depth Expansion Mode (see *Figure 1*)

Depth expansion mode is entered when, during a MR cycle, expansion out (XO) of one device is connected to expansion in (XI) of the next device, with XO of the last device connected to XI of the first device. In the depth expansion mode, the first load (FL) input, when grounded, indicates that this is the first part to be loaded. All other devices must have this pin HIGH. To enable the correct FIFO, XO is pulsed LOW when the last physical location of the previous FIFO is written to and is pulsed LOW again when the last physical location is read. Only one FIFO is enabled for read and one is enabled for write at any given time. All other devices are in standby.

FIFOs can also be expanded simultaneously in depth and width. Consequently, any depth or width FIFO can be created with word widths in increments of nine. When expanding in depth, a composite FF is created by ORing the FFs together. Likewise, a composite EF is created by ORing EFs together. HF and RT functions are not available in depth expansion mode.

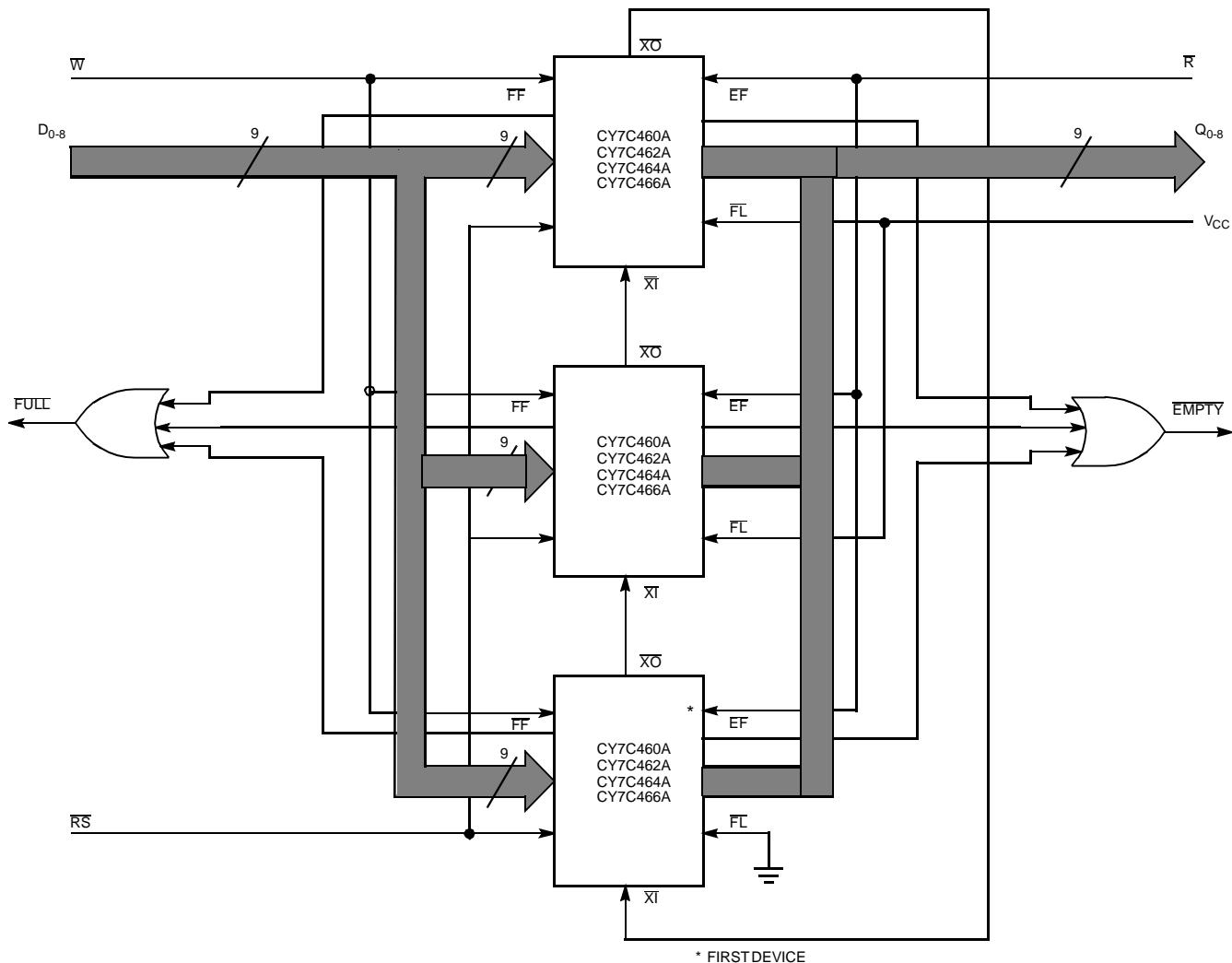


Figure 1. Depth Expansion

**Ordering Information****8K x 9 Asynchronous FIFO**

<b>Speed (ns)</b>	<b>Ordering Code</b>	<b>Package Name</b>	<b>Package Type</b>	<b>Operating Range</b>
10	CY7C460A-10JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C460A-10PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C460A-10PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C460A-10JI	J65	32-Lead Plastic Leaded Chip Carrier	
15	CY7C460A-15JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C460A-15PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C460A-15PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C460A-15JI	J65	32-Lead Plastic Leaded Chip Carrier	
	CY7C460A-15LMB	L55	32-Pin Rectangular Leadless Chip Carrier	Military
25	CY7C460A-25JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C460A-25PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C460A-25PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C460A-25JI	J65	32-Lead Plastic Leaded Chip Carrier	Industrial
	CY7C460A-25LMB	L55	32-Pin Rectangular Leadless Chip Carrier	Military

**16K x 9 Asynchronous FIFO**

<b>Speed (ns)</b>	<b>Ordering Code</b>	<b>Package Name</b>	<b>Package Type</b>	<b>Operating Range</b>
10	CY7C462A-10JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C462A-10PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C462A-10PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C462A-10JI	J65	32-Lead Plastic Leaded Chip Carrier	
15	CY7C462A-15JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C462A-15PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C462A-15PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C462A-15JI	J65	32-Lead Plastic Leaded Chip Carrier	
	CY7C462A-15LMB	L55	32-Pin Rectangular Leadless Chip Carrier	Military
25	CY7C462A-25JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C462A-25PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C462A-25PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C462A-25JI	J65	32-Lead Plastic Leaded Chip Carrier	
	CY7C462A-25LMB	L55	32-Pin Rectangular Leadless Chip Carrier	Military

**Ordering Information (continued)****32K x 9 Asynchronous FIFO**

<b>Speed (ns)</b>	<b>Ordering Code</b>	<b>Package Name</b>	<b>Package Type</b>	<b>Operating Range</b>
10	CY7C464A-10JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C464A-10PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C464A-10PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C464A-10JI	J65	32-Lead Plastic Leaded Chip Carrier	Industrial
15	CY7C464A-15JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C464A-15PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C464A-15PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C464A-15JI	J65	32-Lead Plastic Leaded Chip Carrier	Industrial
	CY7C464A-15LMB	L55	32-Pin Rectangular Leadless Chip Carrier	Military
25	CY7C464A-25JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C464A-25PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C464A-25PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C464A-25JI	J65	32-Lead Plastic Leaded Chip Carrier	Industrial
	CY7C464A-25LMB	L55	32-Pin Rectangular Leadless Chip Carrier	Military

**64K x 9 Asynchronous FIFO**

<b>Speed (ns)</b>	<b>Ordering Code</b>	<b>Package Name</b>	<b>Package Type</b>	<b>Operating Range</b>
10	CY7C466A-10JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C466A-10PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C466A-10PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C466A-10JI	J65	32-Lead Plastic Leaded Chip Carrier	Industrial
15	CY7C466A-15JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C466A-15PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C466A-15PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C466A-15JI	J65	32-Lead Plastic Leaded Chip Carrier	Industrial
	CY7C466A-15LMB	L55	32-Pin Rectangular Leadless Chip Carrier	Military
25	CY7C466A-25JC	J65	32-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C466A-25PC	P15	28-Lead (600-Mil) Molded DIP	
	CY7C466A-25PTC	P21	28-Lead (300-Mil) Molded DIP	
	CY7C466A-25JI	J65	32-Lead Plastic Leaded Chip Carrier	Industrial
	CY7C466A-25LMB	L55	32-Pin Rectangular Leadless Chip Carrier	Military

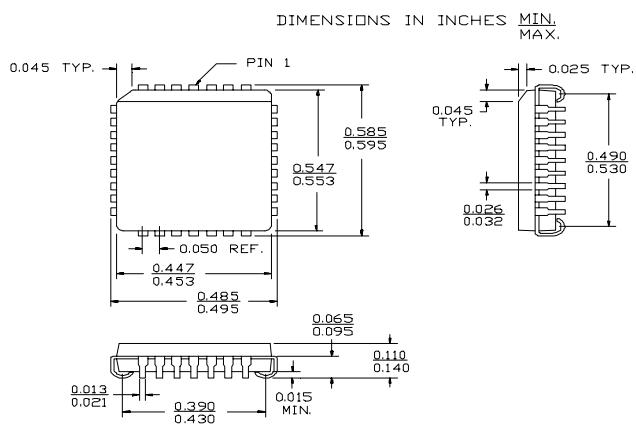
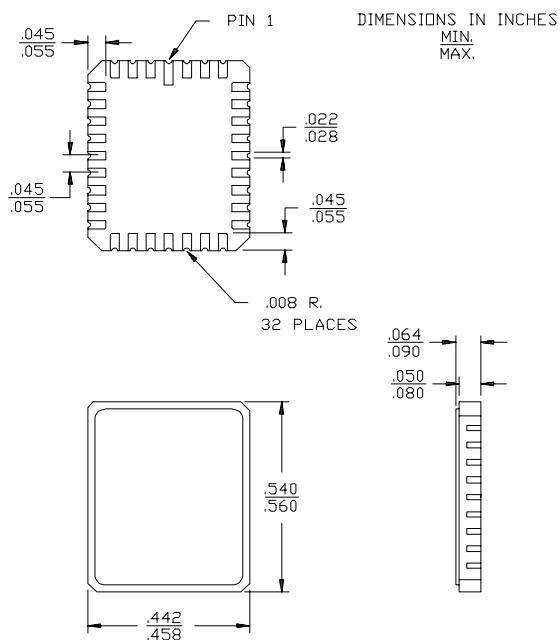
**MILITARY SPECIFICATIONS**  
**Group A Subgroup Testing**
**DC Characteristics**

Parameter	Subgroups
$V_{OH}$	1, 2, 3
$V_{OL}$	1, 2, 3
$V_{IH}$	1, 2, 3
$V_{IL}$ Max.	1, 2, 3
$I_{IX}$	1, 2, 3
$I_{CC}$	1, 2, 3
$I_{SB1}$	1, 2, 3
$I_{SB2}$	1, 2, 3
$I_{os}$	1, 2, 3
$I_{oz}$	1, 2, 3

**Switching Characteristics**

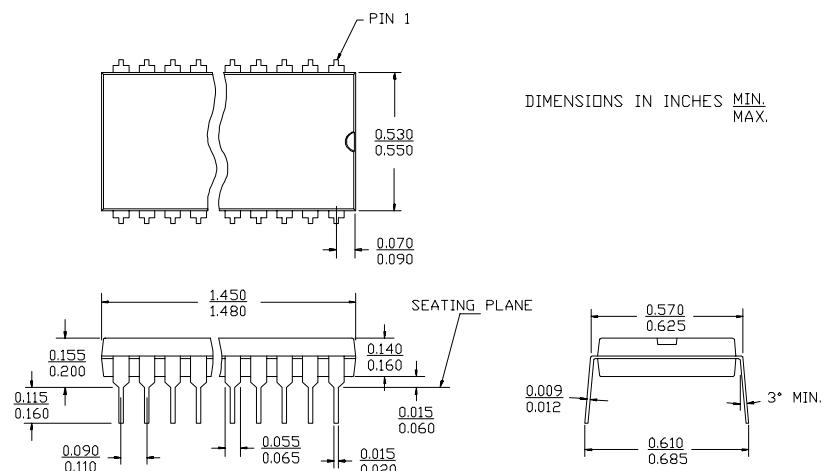
Parameter	Subgroups
$t_{RC}$	9, 10, 11
$t_A$	9, 10, 11
$t_{RR}$	9, 10, 11
$t_{PR}$	9, 10, 11
$t_{LZR}$	9, 10, 11
$t_{DVR}$	9, 10, 11
$t_{HZR}$	9, 10, 11
$t_{WC}$	9, 10, 11
$t_{PW}$	9, 10, 11
$t_{HWZ}$	9, 10, 11
$t_{WR}$	9, 10, 11
$t_{SD}$	9, 10, 11
$t_{HD}$	9, 10, 11
$t_{MRSC}$	9, 10, 11
$t_{PMR}$	9, 10, 11
$t_{RMR}$	9, 10, 11
$t_{RPW}$	9, 10, 11
$t_{WPW}$	9, 10, 11
$t_{RTC}$	9, 10, 11
$t_{PRT}$	9, 10, 11
$t_{RTR}$	9, 10, 11
$t_{EFL}$	9, 10, 11
$t_{HFH}$	9, 10, 11
$t_{FFH}$	9, 10, 11
$t_{REF}$	9, 10, 11
$t_{RFF}$	9, 10, 11
$t_{WEF}$	9, 10, 11
$t_{WFF}$	9, 10, 11
$t_{WHF}$	9, 10, 11
$t_{RHF}$	9, 10, 11
$t_{RAE}$	9, 10, 11
$t_{RPE}$	9, 10, 11
$t_{WAF}$	9, 10, 11
$t_{WPF}$	9, 10, 11
$t_{XOL}$	9, 10, 11
$t_{XOH}$	9, 10, 11

Document #: 38-00627

**Package Diagrams**
**32-Lead Plastic Leaded Chip Carrier J65**

**32-Pin Rectangular Leadless Chip Carrier L55**  
 MIL-STD-1835 C-12


## Package Diagrams (continued)

## 28-Lead (600-Mil) Molded DIP P15



### 28-Lead (300-Mil) Molded DIP P21

